

**IN THE CLAIMS:**

Please amend claims as follows.

1. (original) A heat treatment jig for a semiconductor substrate that is mounted on a heat treatment boat of a vertical heat treatment furnace, comprising:

a semiconductor substrate that is heat treated;

a first jig that is constituted of a silicon material and comes into direct contact with the semiconductor substrate to support; and

a second jig (holder) that holds the first jig and is mounted on the heat treatment boat.

2. (original) A heat treatment jig for a semiconductor substrate according to Claim 1:

wherein the first jig has, in a region that comes into direct contact with the semiconductor substrate, a thickness in the range of from 0.5 to 10 mm, the surface roughness in the range of from 0.02 to 10  $\mu\text{m}$  and the flatness of 100  $\mu\text{m}$  or less; and

the second jig has, in a region that comes into direct contact with the first jig, a thickness in the range of from 0.5 to 10 mm, the surface roughness in the range of from 0.02 to 10  $\mu\text{m}$  and the flatness of 200  $\mu\text{m}$  or less.

3. (original) A heat treatment jig for a semiconductor substrate according to Claim 1:

wherein the first jig is 0.5 mm or more in a width that comes into direct contact with the semiconductor substrate.

4. (original) A heat treatment jig for a semiconductor substrate according to Claim 2:

wherein the first jig is 0.5 mm or more in a width that comes into direct contact with the semiconductor substrate.

5. (currently amended) A heat treatment jig for a semiconductor substrate according to ~~one of Claims 1 through 4~~ Claim 1:

wherein in the first jig, on a surface of a region that comes into direct contact with the semiconductor substrate, any one of a silicon carbide film, an oxide film or a poly-silicon film is formed.

6. (original) A method of heat treating a semiconductor substrate by use of a vertical heat treatment furnace:

wherein a heat treatment jig for a semiconductor substrate that is placed on a heat treatment boat is constituted of a first jig constituted of a silicon material that comes into direct contact with a semiconductor substrate to support and a second jig (holder) that holds the first jig;

wherein the semiconductor substrate held on the first jig is heat treated.

7. (original) A method of heat treating a semiconductor substrate according to Claim 6:

wherein in the case of a slip occurring in a heat treated semiconductor substrate, a position corresponding to the slip in a region that comes into direct contact with the semiconductor substrate of the first jig is ground or polished.

8. (new) A heat treatment jig for a semiconductor substrate according to Claim 2:

wherein in the first jig, on a surface of a region that comes into direct contact with the semiconductor substrate, any one of a silicon carbide film, an oxide film or a poly-silicon film is formed.

9. (new) A heat treatment jig for a semiconductor substrate according to Claim 3:

wherein in the first jig, on a surface of a region that comes into direct contact with the semiconductor substrate, any one of a silicon carbide film, an oxide film or a poly-silicon film is formed.

10. (new) A heat treatment jig for a semiconductor substrate according to Claim 4:

wherein in the first jig, on a surface of a region that comes into direct contact with the semiconductor substrate, any one of a silicon carbide film, an oxide film or a poly-silicon film is formed.